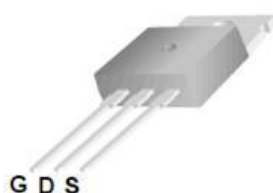


P085AATX

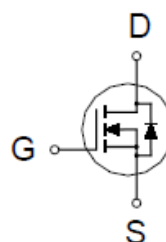
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
55V	7.5m Ω @ $V_{GS} = 10V$	110A



TO-220



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	110	A
	$T_C = 100\text{ }^{\circ}\text{C}$		69	
Pulsed Drain Current ²		I_{DM}	300	
Avalanche Current		I_{AS}	106	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	561	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	166	W
	$T_C = 100\text{ }^{\circ}\text{C}$		66	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		0.75	$^{\circ}\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Limited by maximum junction temperature.

²Limited by package.

P085AATX

N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	55			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 55V, V _{GS} = 0V			1	μA
		V _{DS} = 44V, V _{GS} = 0V , T _J = 125 °C			25	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 62A		6.5	7.5	mΩ
Forward Transconductance ¹	g _{fs}	V _{DS} = 10V, I _D = 62A		96		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		4440		pF
Output Capacitance	C _{oss}			1170		
Reverse Transfer Capacitance	C _{rss}			157		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		2.1		Ω
Total Gate Charge ²	Q _g	V _{DS} = 28V, V _{GS} = 10V, I _D = 62A		92		nC
Gate-Source Charge ²	Q _{gs}			27		
Gate-Drain Charge ²	Q _{gd}			39		
Turn-On Delay Time ²	t _{d(on)}	V _{DD} = 15V, I _D ≅ 62A, V _{GS} = 10V, R _{GEN} = 6Ω		20		nS
Rise Time ²	t _r			110		
Turn-Off Delay Time ²	t _{d(off)}			50		
Fall Time ²	t _f			65		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 °C)						
Continuous Current ³	I _S				110	A
Forward Voltage ¹	V _{SD}	I _F = 62A, V _{GS} = 0V			1.3	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _F = 62 A,		114		nS
Reverse Recovery Charge	Q _{rr}	di _F / dt = 100 A/μs		220		nC

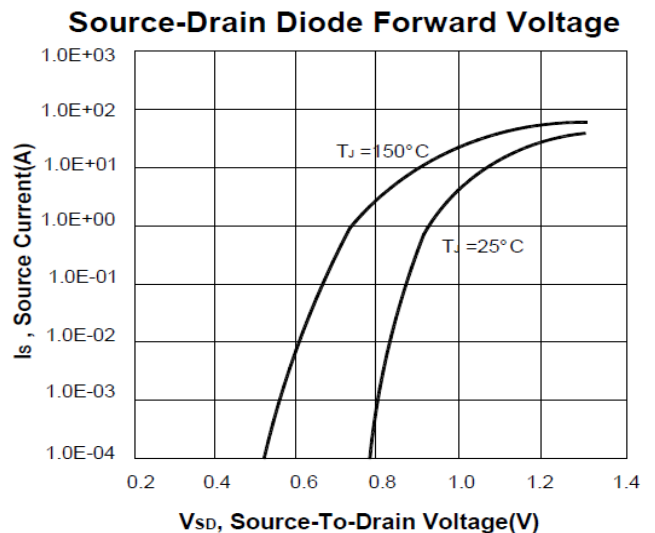
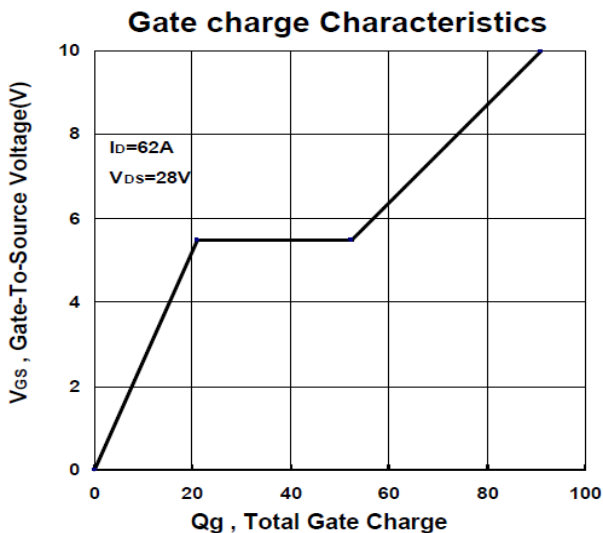
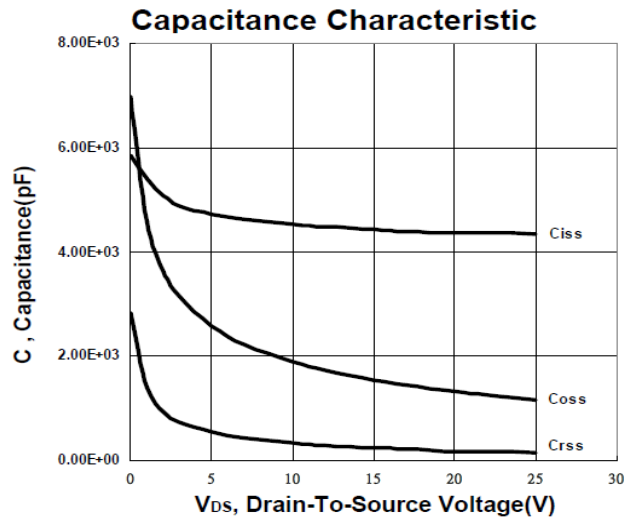
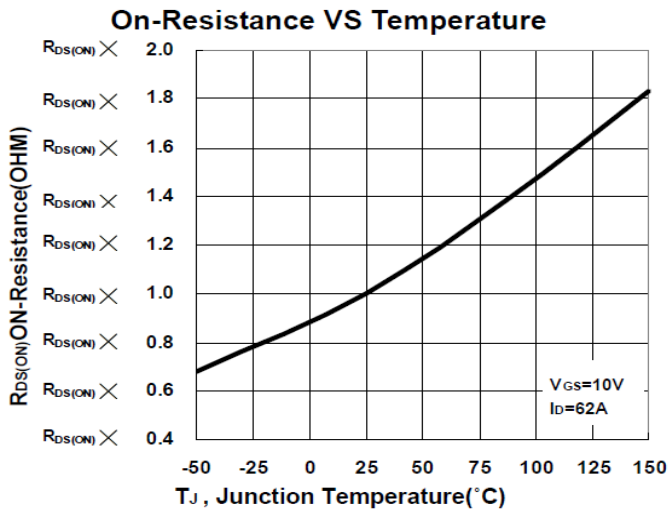
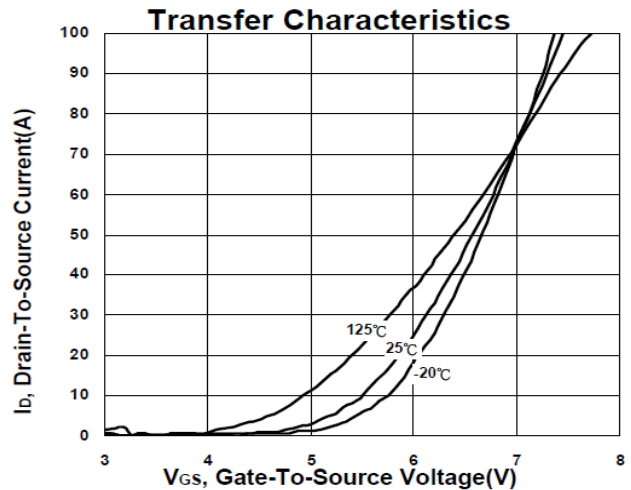
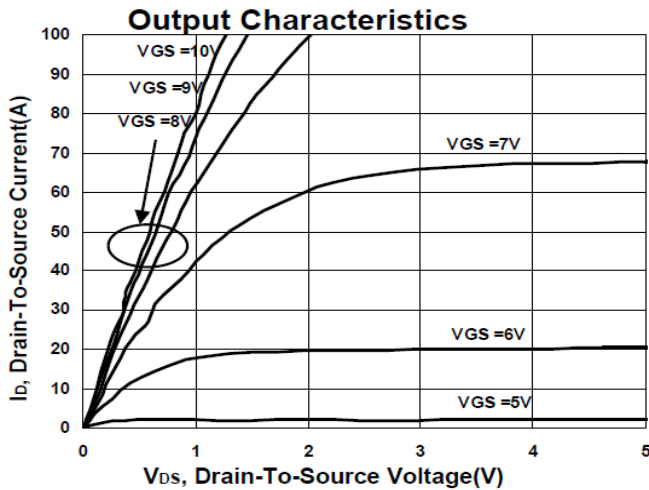
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

³Limited by maximum junction temperature.

P085AATX

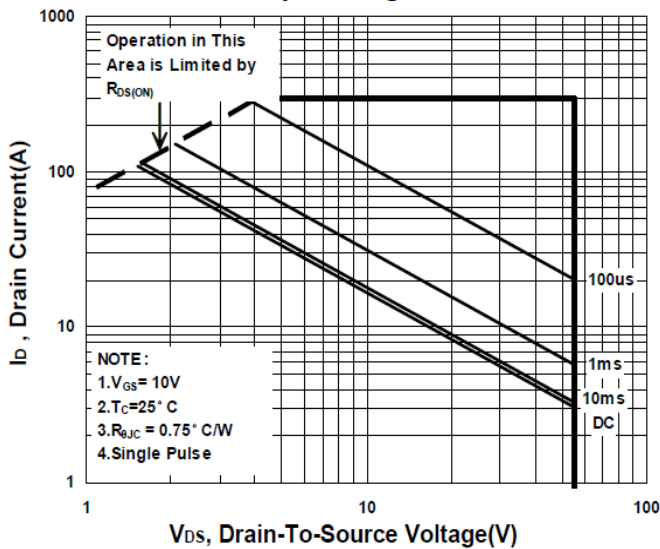
N-Channel Enhancement Mode MOSFET



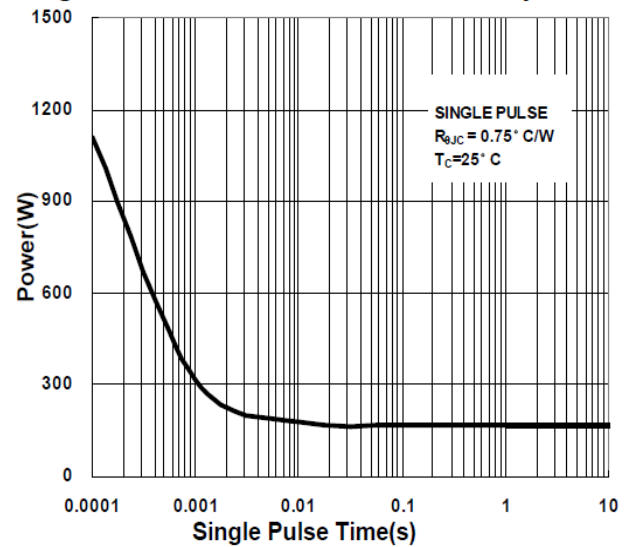
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N-Channel Enhancement Mode MOSFET

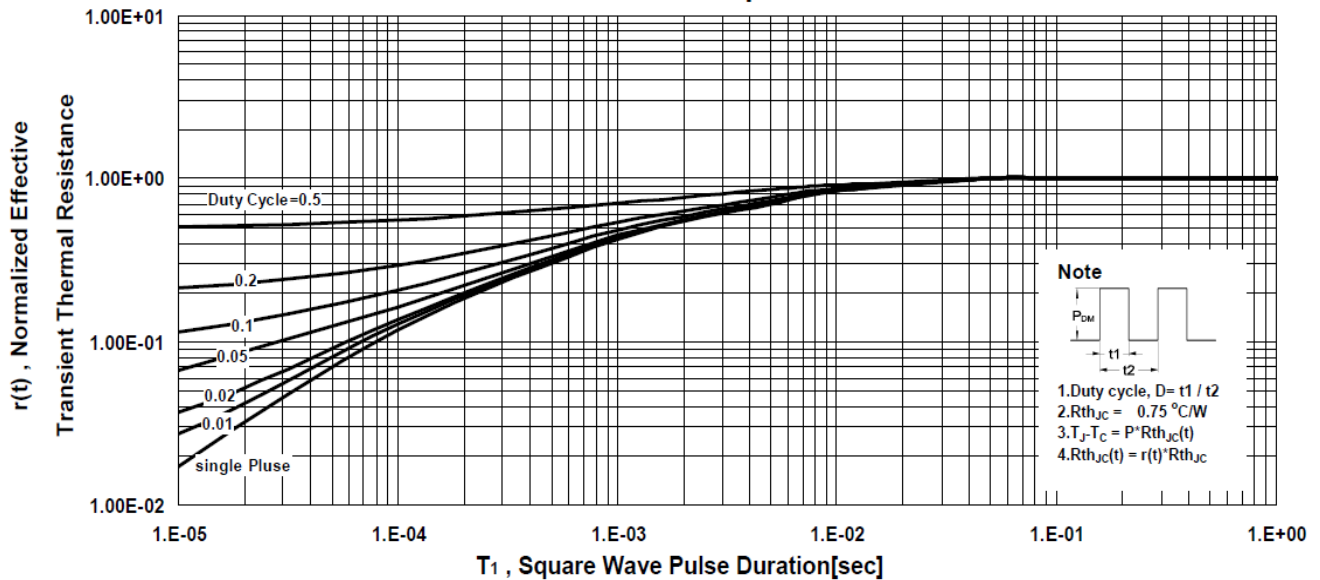
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



P085AATX

N-Channel Enhancement Mode MOSFET

Package Dimension

TO-220 (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.652	10.16	11.5	H	2.04	2.54	3.04
B	2.54	2.79	3.048	I	1.15	1.52	1.778
C	17.3		22.86	J	3.556	4.57	4.826
D	26.924	29.03	31.242	K	0.508	1.3	1.45
E	14.224	15.45	16.510	L	1.89	2.69	3.09
F	8.382	9.20	9.40	M	0.34	0.5	0.6
G	0.381	0.81	1.016	N			

